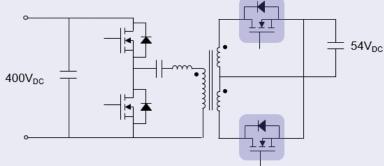


## 150 V, 5.6 m $\Omega$ SiRS5700DP MOSFET in PowerPAK<sup>®</sup> SO-8S Increases Efficiency With Industry-Low R<sub>DS(ON)</sub> and R<sub>DS(ON)</sub>\*Q<sub>g</sub> FOM

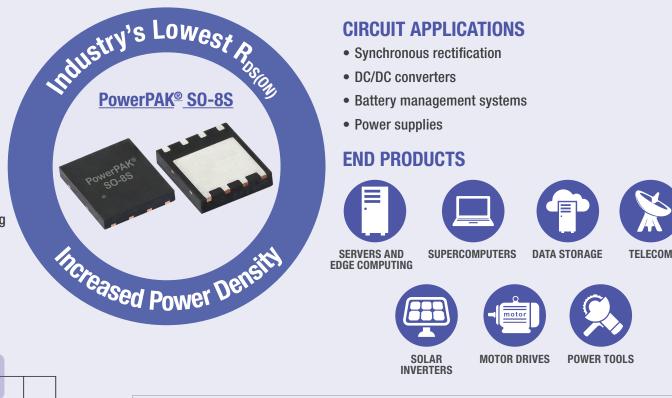
## **FEATURES**

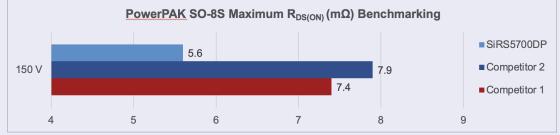
- Typical  $R_{DS(ON)} = 4.6 \text{ m}\Omega$
- Industry's lowest R<sub>DS(ON)</sub>\*Q<sub>q</sub> FOM
- Complies with IPC-9701 criteria for more reliable temperature cycling
- Standard 6 mm by 5 mm footprint is fully compatible with the PowerPAK® S0-8 package
- Available in PowerPAK<sup>®</sup> SO-8S (QFN 6x5) package
  - Offers extremely low 0.45 °C/W R<sub>thJC</sub>, enabling continuous drain current up to 144 A to increase power density, while providing robust SOA capability

## **TYPICAL CIRCUIT DIAGRAM**



SiRS5700DP for the 54  $\rm V_{out}$  secondary side of an LLC resonant converter with a central tap transformer.





Compared to the nearest competitors, the SiRS5700DP offers the industry's lowest  $R_{DS(0N)}$  — with an improvement of at least 24.3 % — which is ideal for next-generation power supply requirements, such as 6 kW AI server power systems.

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